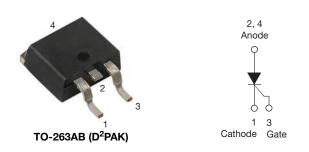


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# **Thyristor Surface Mount Phase Control SCR, 16 A**



PRODUCT SUMMARY						
Package	TO-263AB (D <sup>2</sup> PAK)					
Diode variation	Single SCR					
I <sub>T(AV)</sub>	10 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V					
V <sub>TM</sub>	1.4 V					
I <sub>GT</sub>	60 mA					
TJ	-40 °C to 125 °C					

#### **FEATURES**

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **APPLICATIONS**

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

#### **DESCRIPTION**

The VS-16TTS16SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5						

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	10	۸					
I <sub>RMS</sub>		16	Α Α					
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V					
I <sub>TSM</sub>		200	А					
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
T <sub>J</sub>		-40 to 125	°C					

VOLTAGE RATINGS										
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA							
VS-16TTS16SPbF	1600	1600	10							



ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES					
PARAMETER	STIVIBUL	TEST CONDITIONS	TYP.	TYP. MAX.					
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C = 93$ °C, 180° conduction, half sine wave	1	10					
Maximum RMS on-state current	I <sub>RMS</sub>		1	6	Α				
Maximum peak, one-cycle,	I	10 ms sine pulse, rated V <sub>RRM</sub> applied	1	70					
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	2	00	ļ				
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	1-	144					
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	2	200					
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied	2000		A²√s				
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C	1.4		V				
On-state slope resistance	r <sub>t</sub>	T <sub>.I</sub> = 125 °C	24.0		mΩ				
Threshold voltage	V <sub>T(TO)</sub>	IJ = 125 C	1	.1	V				
Maximum roverse and direct lookeds current	1 /1	$T_J = 25  ^{\circ}C$	0	.5					
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$V_R = Rated V_{RRM}/V_{DRM}$	1	0					
Holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A $T_J$ = 25 °C	100	150	mA				
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2	200					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = Rg - k = Open$	500		V/µs				
Maximum rate of rise of turned-on current	dl/dt		1:	150					

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	$P_{GM}$		8.0	W				
Maximum average gate power	$P_{G(AV)}$		2.0	VV				
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α				
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90					
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60	mA				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V				
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detect value	0.25					
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA				

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9						
Typical reverse recovery time	t <sub>rr</sub>	T. – 105 °C	4	μs					
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110						

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C				
Soldering temperature	T <sub>S</sub>	T <sub>S</sub> For 10 s (1.6 mm from case)						
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.3	°C/W				
Typical thermal resistance, junction to ambient	R <sub>thJA</sub>	PCB mount (1)	40	C/VV				
Approximate weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D <sup>2</sup> PAK (SMD-220)	16TTS	16S				

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

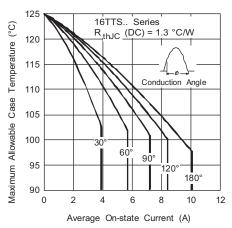


Fig. 1 - Current Rating Characteristics

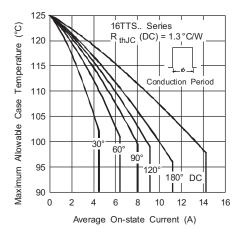


Fig. 2 - Current Rating Characteristics

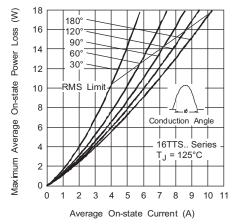


Fig. 3 - On-State Power Loss Characteristics

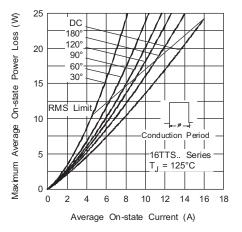


Fig. 4 - On-State Power Loss Characteristics

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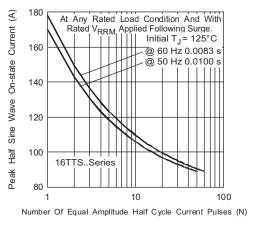


Fig. 5 - Maximum Non-Repetitive Surge Current

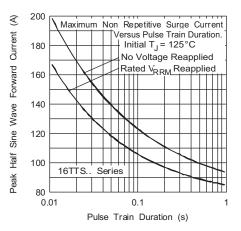


Fig. 6 - Maximum Non-Repetitive Surge Current

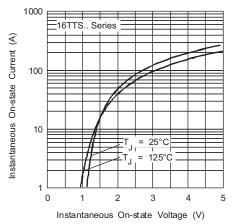


Fig. 7 - On-State Voltage Drop Characteristics

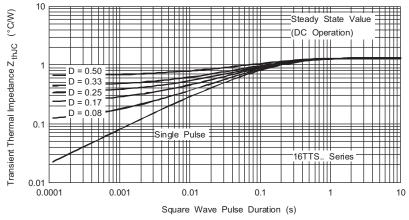


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

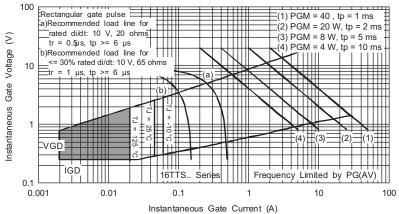
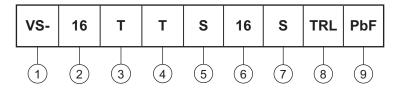


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

### **Device code**



- Vishay Semiconductors product
- 2 Current rating
- Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AC

5 - Type of silicon:

S = standard recovery rectifier

- 6 Voltage rating: Voltage code x 100 = V<sub>RRM</sub> (16 = 1600 V)
- 7 S = TO-220 D<sup>2</sup>PAK (SMD-220) version
- 8 • None = tube
  - TRL = tape and reel (left oriented)
  - TRR = tape and reel (right oriented)
- 9 PbF = lead (Pb)-free

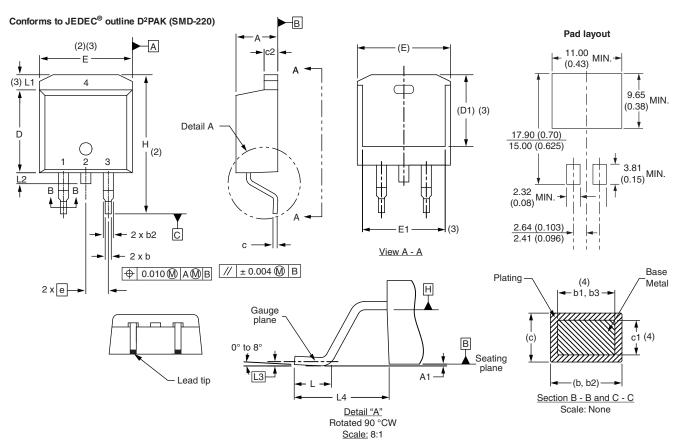
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-16TTS16SPbF	50	1000	Antistatic plastic tubes					
VS-16TTS16STRRPbF	800	800	13" diameter reel					
VS-16TTS16STRLPbF	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95046</u>					
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				



### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

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